
2SK2216

Silicon N-Channel MOS FET

HITACHI

ADE-208-346A
2nd. Edition

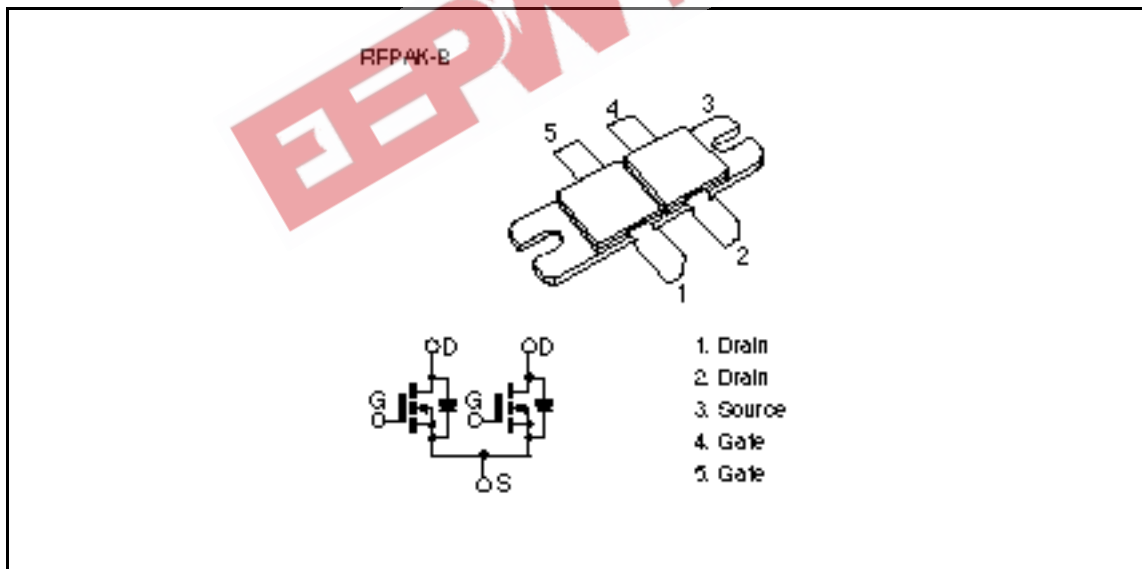
Application

UHF power amplifier

Features

- High power output, high gain, high efficiency
PG = 9.7 dB, Pout = 140 W, D = 55% typ (f = 860 MHz)
- Compact package
Suitable for push - pull circuit

Outline



2SK2216

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	±10	V
Drain current	I _D	20	A
Channel dissipation	Pch* ¹	150	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

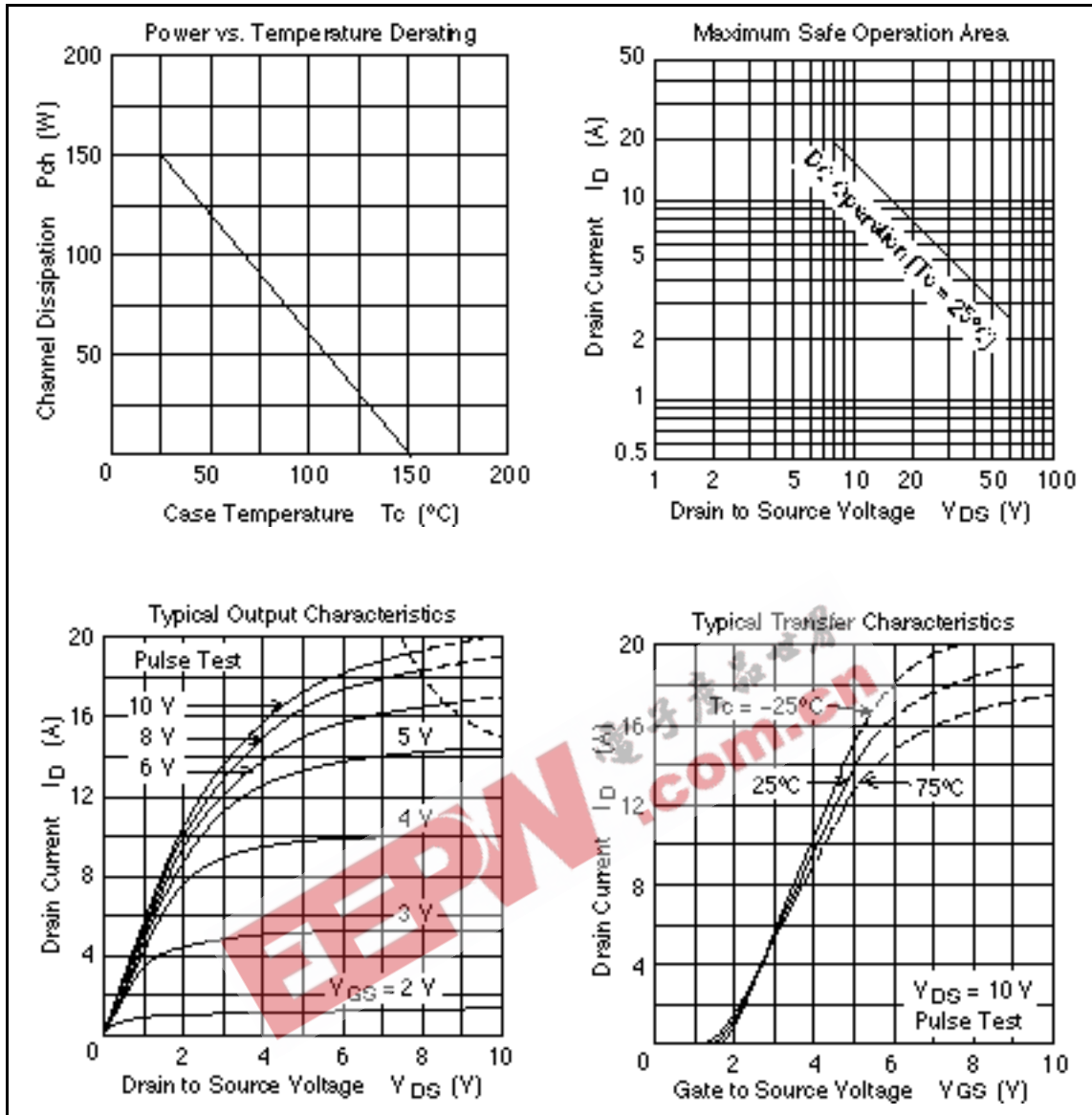
Note: 1. Value at T_C = 25°C

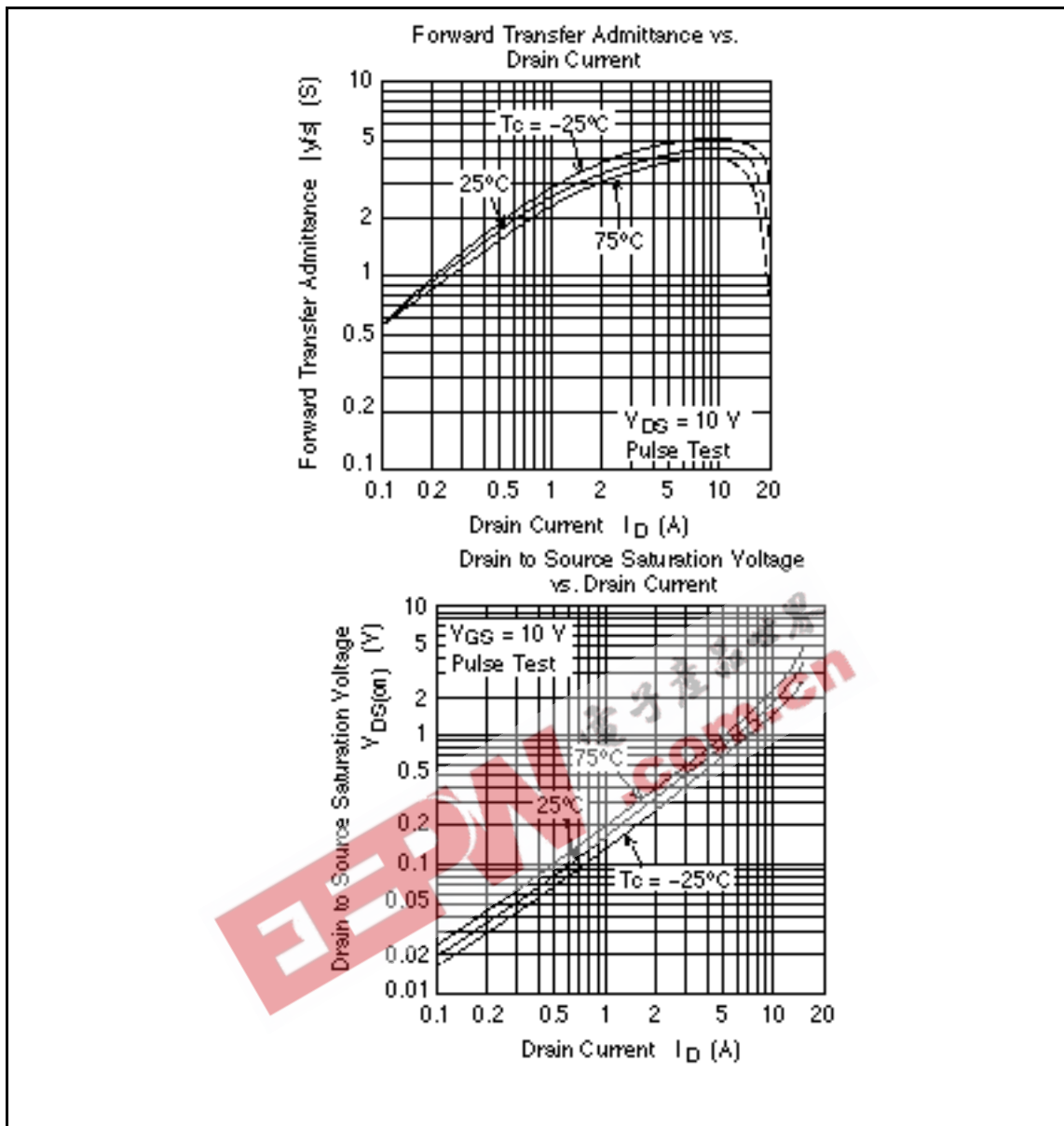
Electrical Characteristics (T_C = 25°C)

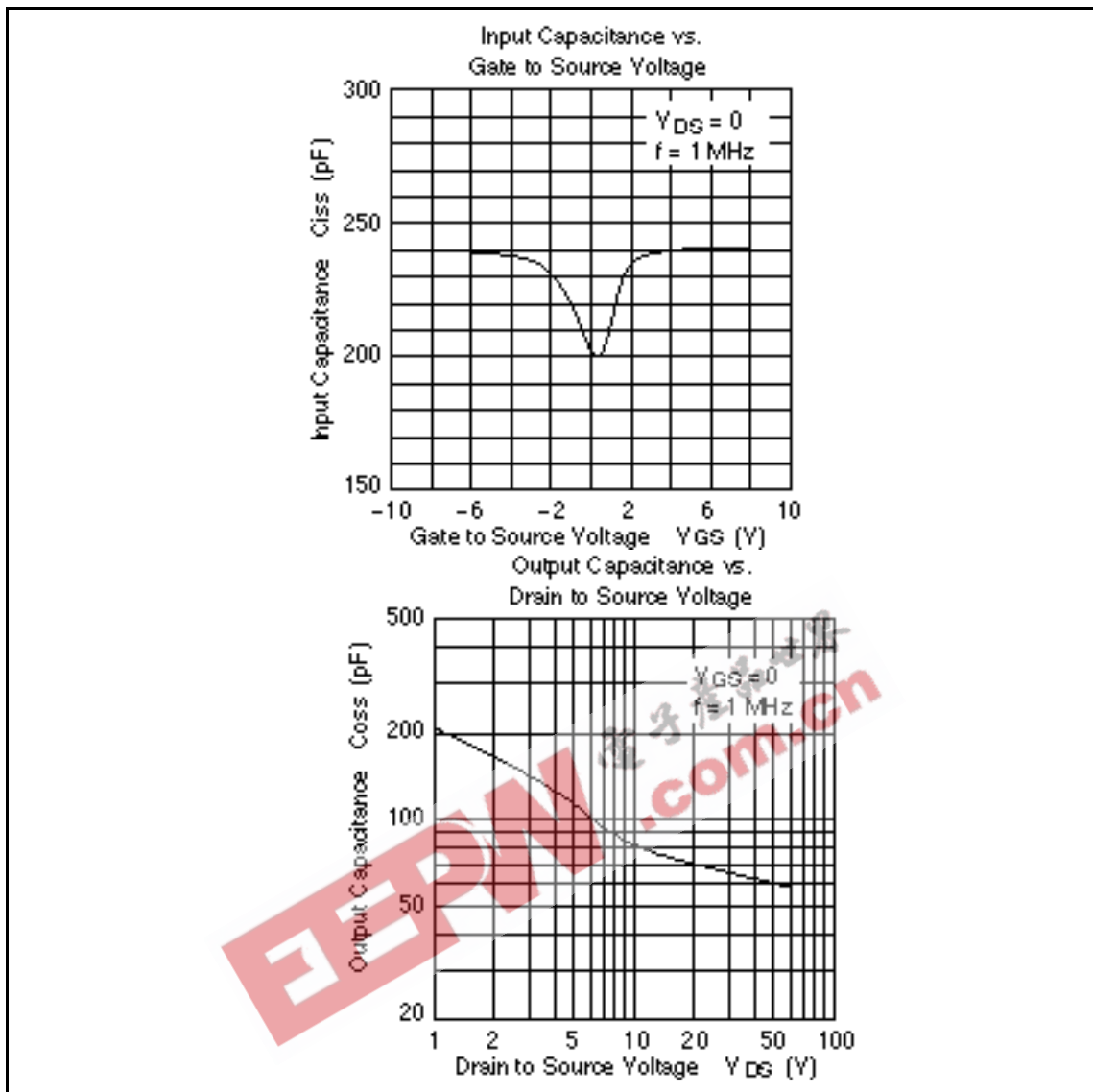
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain leakage current* ¹	I _{DSS}	—	—	1	mA	V _{DS} = 60 V, V _{GS} = 0
Gate leakage current* ¹	I _{GSS}	—	—	± 3	μA	V _{GS} = ± 10 V, V _{DS} = 0
Gate to source cutoff voltage* ¹	V _{GS(off)}	0.3	—	1.6	V	V _{DS} = 10 V, I _D = 1 mA
Drain to source voltage* ¹	V _{DS(on)}	—	1.2	2.5	V	V _{GS} = 10 V, I _D = 5 A* ²
Forward transfer admittance* ¹	y _{fs}	3.0	4.0	—	S	V _{DS} = 10 V, I _D = 5 A* ²
Input capacitance* ¹	C _{iss}	—	250	—	pF	V _{GS} = 5 V, V _{DS} = 0 f = 1MHz
Output capacitance* ¹	C _{oss}	—	85	—	pF	V _{DS} = 10V, V _{GS} = 0 f = 1MHz
Output power	P _{OUT}	100	140	—	W	V _{DS} = 28 V, I _{DO} = 0.4 A
Drain efficiency	D	—	55	—	%	f = 860 MHz, Pin = 15 W

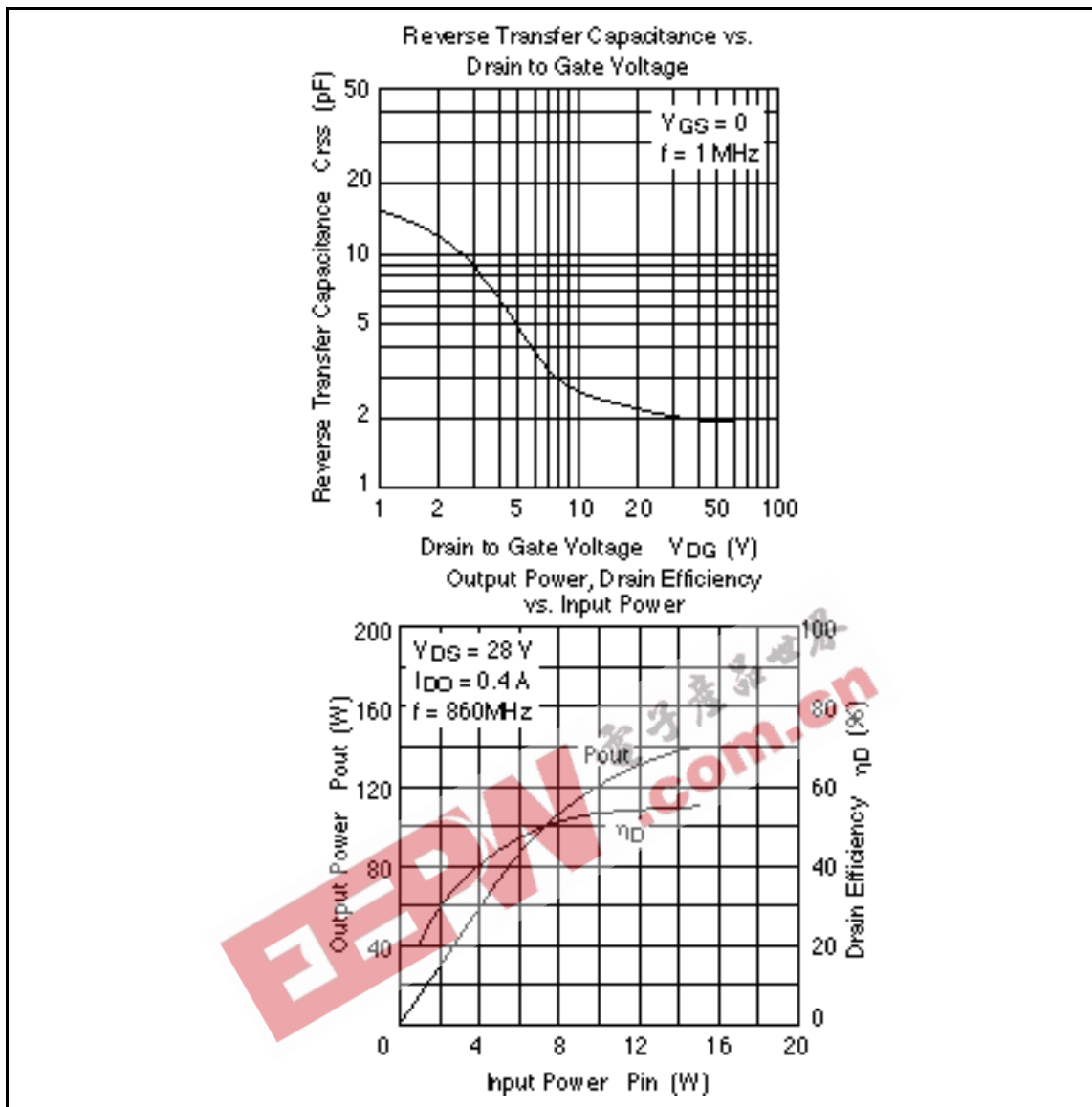
Notes: 1. Shows / unit FET

2. Pulse Test



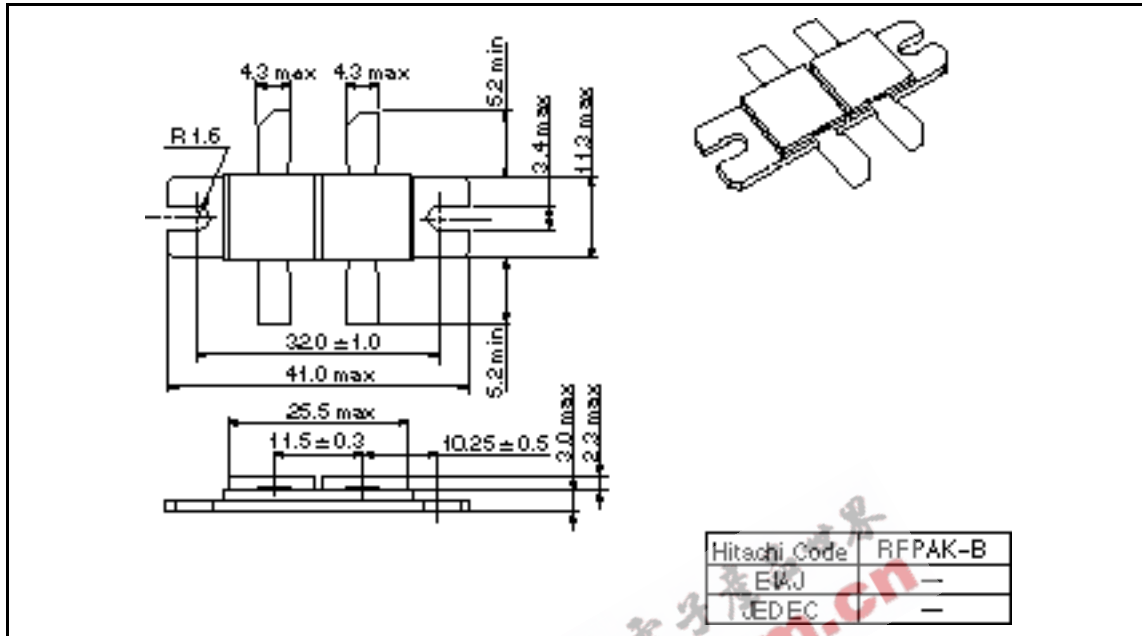






Package Dimensions

Unit: mm



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